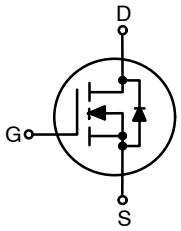
# Transistor - N-Channel, Logic Level, Enhancement Mode Field Effect

# FDN337N




**SOT−23−3**
**CASE 527AG**

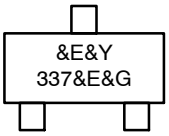
## General Description

SUPERSOT™ −3 N−Channel logic level enhancement mode power field effect transistors are produced using **onsemi**'s proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on−state resistance. These devices are particularly suited for low voltage applications in notebook computers, portable phones, PCMCIA cards, and other battery powered circuits where fast switching, and low in−line power loss are needed in a very small outline surface mount package.

## Features

- 2.2 A, 30 V
  - $R_{DS(on)}$ = 0.065 Ω @ $V_{GS}$ = 4.5 V
  - $R_{DS(on)}$ = 0.082 Ω @ $V_{GS}$ = 2.5 V
- Industry Standard Outline SOT−23 Surface Mount Package Using Proprietary SUPERSOT−3 Design for Superior Thermal and Electrical Capabilities
- High Density Cell Design for Extremely Low $R_{DS(on)}$
- Exceptional on−Resistance and Maximum DC Current Capability
- This Device is Pb−Free and Halogen Free

## MARKING DIAGRAM




&E = Designates Space
&Y = Binary Calendar Year Coding Scheme
337 = Specific Device Code
&G = Date Code

## ORDERING INFORMATION

| Device | Package | Shipping† |
|---|---|---|
| FDN337N | SOT−23−3 (Pb−Free) | 3000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

## ABSOLUTE MAXIMUM RATINGS

$T_A$ = 25°C unless otherwise noted.

| Symbol | Parameter | Ratings | Unit |
|---|---|---|---|
| $V_{DSS}$ | Drain−Source Voltage | 30 | V |
| $V_{GSS}$ | Gate−Source Voltage − Continuous | ±8 | V |
| $I_D$ | Drain/Output Current − Continuous | 2.2 | A |
| | Drain/Output Current − Pulsed | 10 | |
| $P_D$ | Maximum Power Dissipation (Note 1a) | 0.5 | W |
| | Maximum Power Dissipation (Note 1b) | 0.46 | |
| $T_J$, $T_{STG}$ | Operating and Storage Temperature Range | −55 to +150 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## THERMAL CHARACTERISTICS

$T_A$ = 25°C unless otherwise noted.

| Symbol | Parameter | Ratings | Unit |
|---|---|---|---|
| $R_{\theta JA}$ | Thermal Resistance, Junction−to−Ambient (Note 1a) | 250 | °C/W |
| $R_{\theta JC}$ | Thermal Resistance, Junction−to−Case (Note 1) | 75 | °C/W |

**ELECTRICAL CHARACTERISTICS** $T_A$ = 25°C unless otherwise noted.

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS** | | | | | | |
| $BV_{DSS}$ | Drain–Source Breakdown Voltage | $V_{GS}$ = 0 V, $I_D$ = 250 μA | 30 | – | – | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D$ = 250 μA, Referenced to 25°C | – | 41 | – | mV/°C |
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{DS}$ = 24 V, $V_{GS}$ = 0 V | – | – | 1 | μA |
| | | $V_{DS}$ = 24 V, $V_{GS}$ = 0 V, $T_J$ = 55°C | – | – | 10 | |
| $I_{GSSF}$ | Gate–Body Leakage, Forward | $V_{GS}$ = 8 V, $V_{DS}$ = 0 V | – | – | 100 | nA |
| $I_{GSSR}$ | Gate–Body Leakage, Reverse | $V_{GS}$ = −8 V, $V_{DS}$ = 0 V | – | – | −100 | nA |
| **ON CHARACTERISTICS** (Note 2) | | | | | | |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}$ = $V_{GS}$, $I_D$ = 250 μA | 0.4 | 0.7 | 1 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate Threshold Voltage Temperature Coefficient | $I_D$ = 250 μA, Referenced to 25°C | – | −2.3 | – | mV/°C |
| $R_{DS(on)}$ | Static Drain–Source On–Resistance | $V_{GS}$ = 4.5 V, $I_D$ = 2.2 A | – | 0.054 | 0.065 | Ω |
| | | $V_{GS}$ = 4.5 V, $I_D$ = 2.2 A, $T_J$ = 125°C | – | 0.08 | 0.11 | |
| | | $V_{GS}$ = 2.5 V, $I_D$ = 2 A | – | 0.07 | 0.082 | |
| $I_{D(on)}$ | On–State Drain Current | $V_{GS}$ = 4.5 V, $V_{DS}$ = 5 V | 10 | – | – | A |
| $g_{FS}$ | Forward Transconductance | $V_{DS}$ = 5 V, $I_D$ = 2.2 A | – | 13 | – | S |
| **DYNAMIC CHARACTERISTICS** | | | | | | |
| $C_{iss}$ | Input Capacitance | $V_{DS}$ = 10 V, $V_{GS}$ = 0 V, f = 1.0 MHz | – | 300 | – | pF |
| $C_{oss}$ | Output Capacitance | | – | 145 | – | |
| $C_{rss}$ | Reverse Transfer Capacitance | | – | 35 | – | |
| **SWITCHING CHARACTERISTICS** (Note 2) | | | | | | |
| $t_{d(on)}$ | Turn–On Delay Time | $V_{DD}$ = 5 V, $I_D$ = 1 A, $V_{GS}$ = 4.5 V, $R_{GEN}$ = 6 Ω | – | 4 | 10 | ns |
| $t_r$ | Turn–On Rise Time | | – | 10 | 18 | |
| $t_{d(off)}$ | Turn–Off Delay Time | | – | 17 | 28 | |
| $t_f$ | Turn–Off Fall Time | | – | 4 | 10 | |
| $Q_g$ | Total Gate Charge | $V_{DS}$ = 10 V, $I_D$ = 2.2 A, $V_{GS}$ = 4.5 V | – | 7 | 9 | nC |
| $Q_{gs}$ | Gate–Source Charge | | – | 1.1 | – | |
| $Q_{gd}$ | Gate–Drain Charge | | – | 1.9 | – | |
| **DRAIN–SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS** | | | | | | |
| $I_S$ | Maximum Continuous Drain–Source Diode Forward Current | | – | – | 0.42 | A |
| $V_{SD}$ | Drain–Source Diode Forward Voltage | $V_{GS}$ = 0 V, $I_S$ = 0.42 A (Note 2) | – | 0.65 | 1.2 | V |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTE:

1. $R_{\theta JA}$ is the sum of the junction–to–case and case–to–ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.
   Typical $R_{\theta JA}$ using the board layouts shown below on FR–4 PCB in a still air environment:

   a) 250°C/W when mounted on a 0.02 $in^2$ pad of 2 oz. copper.

   b) 270°C/W when mounted on a 0.001 $in^2$ pad of 2 oz. copper.

   Scale 1:1 on letter size paper

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

## TYPICAL CHARACTERISTICS

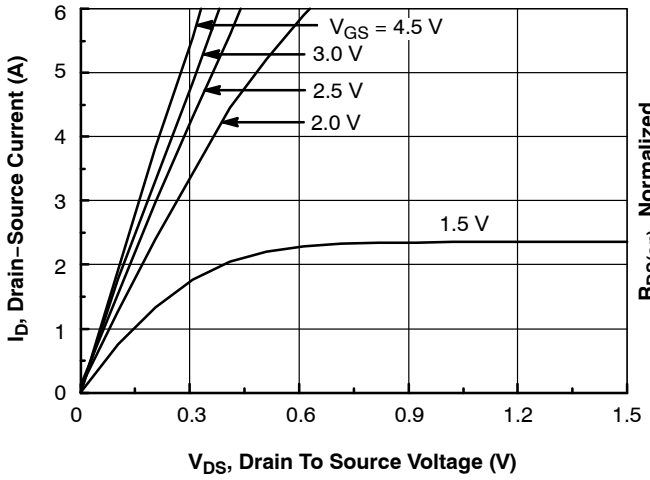



**Figure 1. On−Region Characteristics**

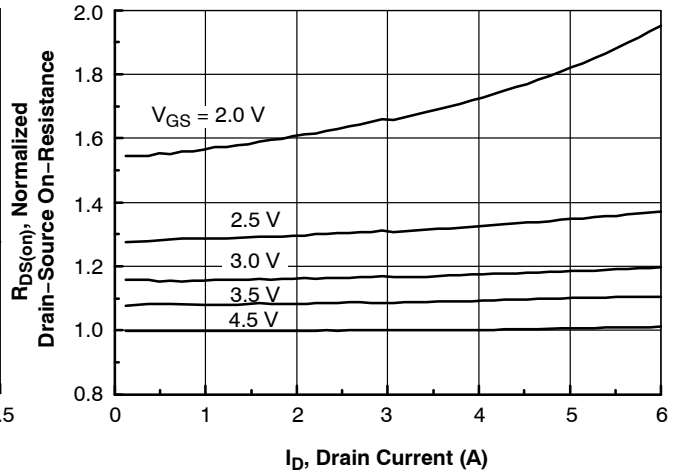



**Figure 2. On−Resistance Variation with Drain Current and Gate Voltage**

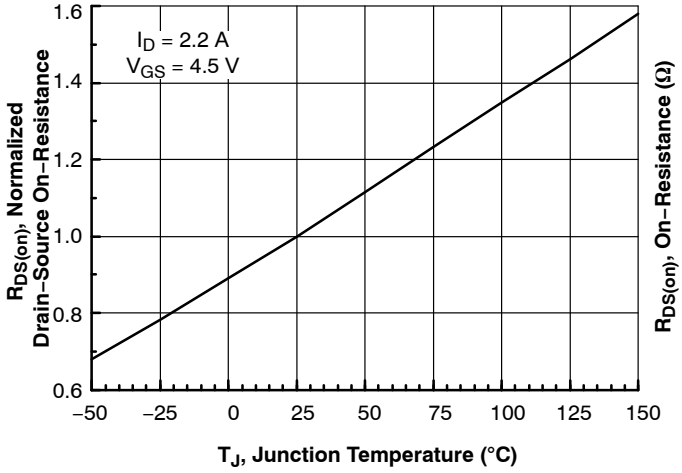



**Figure 3. On−Resistance Variation with Temperature**

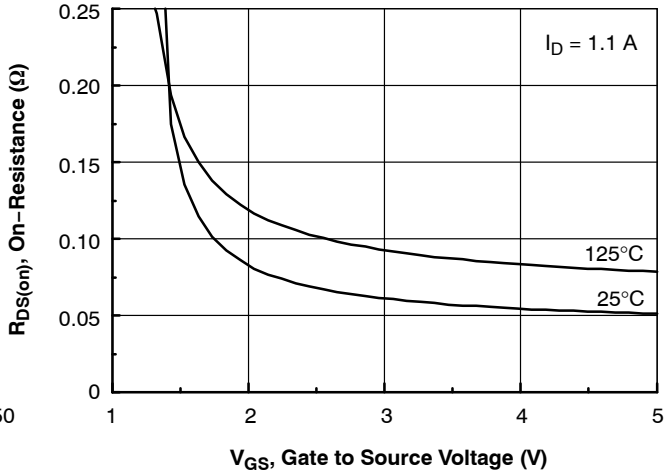



**Figure 4. On−Resistance Variation with Gate−to−Source Voltage**

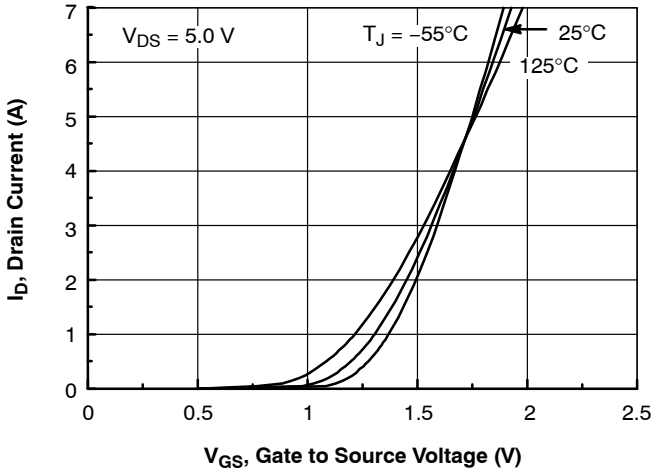



**Figure 5. Transfer Characteristics**

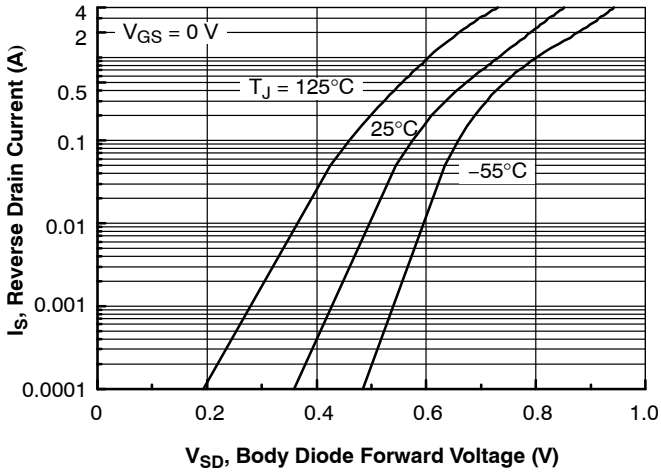



**Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature**

## TYPICAL CHARACTERISTICS (continued)

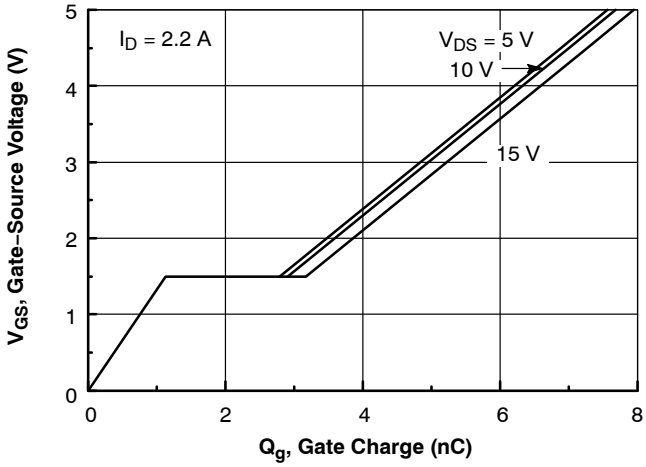



**Figure 7. Gate Charge Characteristics**

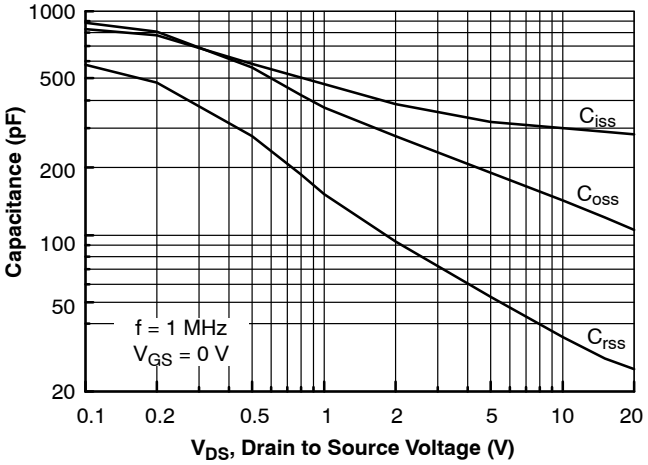



**Figure 8. Capacitance Characteristics**

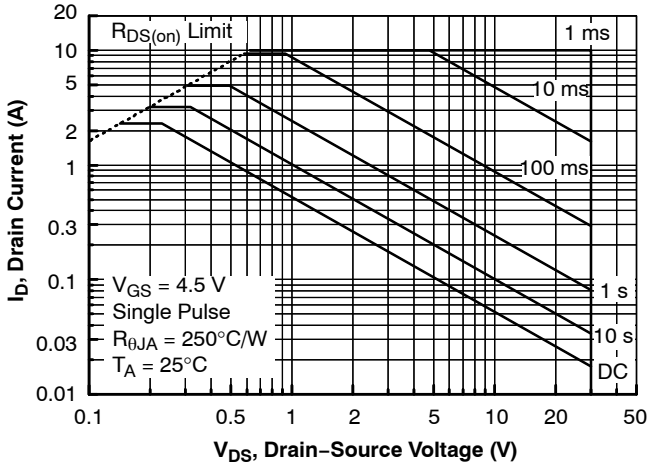



**Figure 9. Maximum Safe Operating Area**

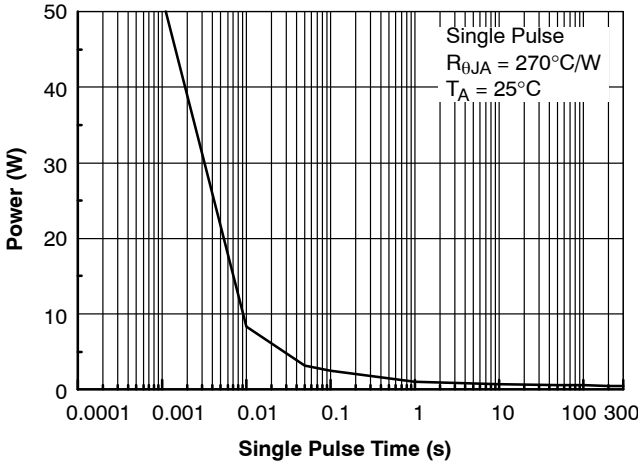



**Figure 10. Single Pulse Maximum Power Dissipation**

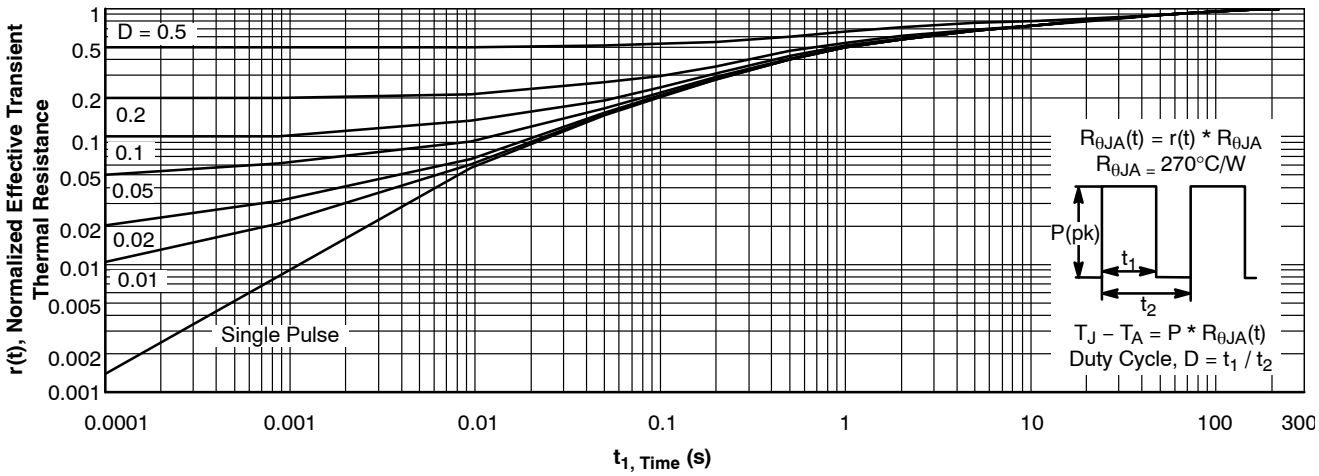
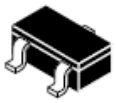


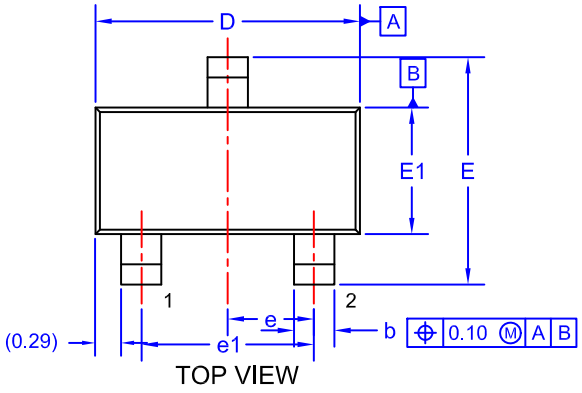

**Figure 11. Transient Thermal Response Curve**

Thermal characterization performed using the conditions described in Note 1b.
Transient thermal response will change depending on the circuit board design.



**SOT−23/SUPERSOT™ −23, 3 LEAD, 1.4x2.9**
CASE 527AG
ISSUE A

DATE 09 DEC 2019

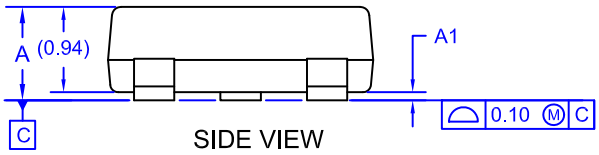


TOP VIEW

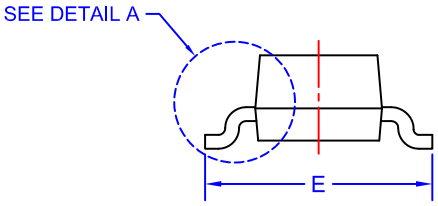
NOTES: UNLESS OTHERWISE SPECIFIED

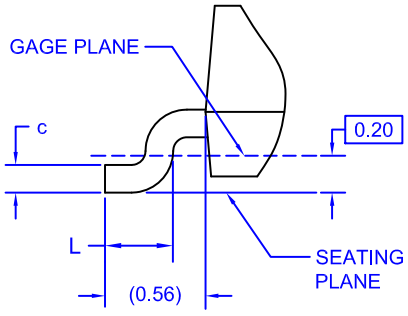
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. ALL DIMENSIONS ARE IN MILLIMETERS.
3. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.

| DIM | MIN. | NOM. | MAX. |
|---|---|---|---|
| A | 0.85 | 0.95 | 1.12 |
| A1 | 0.00 | 0.05 | 0.10 |
| b | 0.370 | 0.435 | 0.508 |
| c | 0.085 | 0.150 | 0.180 |
| D | 2.80 | 2.92 | 3.04 |
| E | 2.31 | 2.51 | 2.71 |
| E1 | 1.20 | 1.40 | 1.52 |
| e | 0.95 BSC | | |
| e1 | 1.90 BSC | | |
| L | 0.33 | 0.38 | 0.43 |

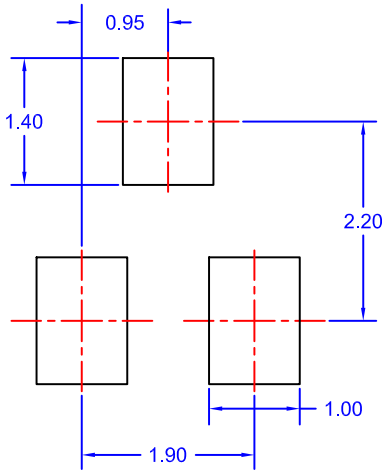


SIDE VIEW



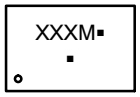
DETAIL A



LAND PATTERN RECOMMENDATION*

*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

**GENERIC MARKING DIAGRAM***




XXX = Specific Device Code
M = Month Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

| | | |
|---|---|---|
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| **DESCRIPTION:** | **SOT−23/SUPERSOT−23, 3 LEAD, 1.4X2.9** | **PAGE 1 OF 1** |

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